## 法政大学学術機関リポジトリ

## HOSEI UNIVERSITY REPOSITORY

PDF issue: 2025-01-15

## **CONTENTS**

(出版者 / Publisher) 法政大学イオンビーム工学研究所

(雑誌名 / Journal or Publication Title)

PROCEEDINGS OF THE 37th SYMPOSIUM ON MATERIALS SCIENCE AND ENGINEERING RESEARCH CENTER OF ION BEAM TECHNOLOGY HOSEI UNIVERSITY (December 5, 2018)

(巻 / Volume)

37

(発行年 / Year)

2019-02

## CONTENTS

I.	Invited Papers
1.	MECHANISM OF ELONGATION OF GOLD NANOPARTICLES EMBEDDED IN SILICA GLASS  K. AWAZU ····································
2.	ANALYSIS OF IRRADIATED MATERIALS BY INTENSE SLOW POSITRON BEAMS
	A. KINOMURA3
Π.	Contributed Papers
1.	DAMAGE-FREE FABRICATION OF HIGH BREAKDOWN VOLTAGE GaN p-n JUNCTION DIODES BY
	WET ETCHING PROCESS
	N. ASAI, H. OHTA, F. HORIKIRI, Y. NARITA, T. YOSHIDA, and T. MISHIMA······7
2.	GaN p-n JUNCTION DIODES WITH HIGH REVERSE RECOVERY CAPABILITY
	H. OHTA, N. ASAI, F. HORIKIRI, Y. NARITA, T. YOSHIDA, and T. MISHIMA·······13
3.	ANNEALING EFFECTS ON Ce/Si MIXED COMPOUND OXIDES DEPOSITED
	BY RF MAGNETRON CO-SPUTTERING
	T. TAKAZAWA, R. KOMATSU, S. SUZUKI, K. ISHIBASHI, and Y. YAMAMOTO······19
4.	ELECTRICAL PROPERTIES OF Al $_2O_3$ INCORPORATED CeO $_2$ COMPOSITION SPREAD FILMS
	USING COMBINATORIAL SPUTTERING SYSTEM
	T. GOTO, J. KONISHI, S. SUZUKI, K. ISHIBASHI, and Y. YAMAMOTO······27
5.	EVALUATION OF Ce-Si COMPOUND OXIDE FILMS BY HYDROLYTIC MOCVD
	T. WADA, K. KIKUCHI, S. SUZUKI, K. ISHIBASHI, and Y. YAMAMOTO · · · · · 37
6.	
7.	EVALUATION BY THERMAL DESORPTION METHOD OF Cs -Sb COMPOUND
	PHOTOCATHODE DEPOSITED ON GaAs SUBSTRATE
	M. MAEDA, H. IIJIMA, and T. MEGURO49

8.	FORMATION OF MICRO/NANO STRUCTURES ALLEY AND DEVELOPMENT OF
	SURFACE CLEANING PROCEDURE FOR NEA-GaAs SURFACES
	D. ISHIKAWA, M. HIRAO, H. NISHIKAWA, and T. MEGURO53
9.	ANALYSIS OF RADIOACTIVE Cs-CONTAINING MICROPARTICLE BY R-SNMS
	Y. MIYASHITA, M. MORITA, and T. SAKAMOTO······59
10.	ANALYSIS OF DISSOLVED COMPONENTS FROM DIESEL SOOT PARTICLES
	K. TAKANO, R. KOIWAI, M. MORITA, and T. SAKAMOTO63
11.	DEVELOPMENT OF RAPID FREEZING METHOD FOR WATER-CONTAINING CANCER
	CELLS FOR TOF-SIMS ANALYSIS
	T. HASEGAWA, K. TAMURA, M. MORITA, K. NAGASE, M. KAKIHANA, N. KAJIWARA, T. OHIRA,
	N. IKEDA, and T. SAKAMOTO 67
12.	THE EPITAXIAL GROWTH OF AMORPHOUS SI LAYER DEPOSITED ON
	HYDROGEN-TERMINATED SURFACES USING ION BEAM INDUCED EPITAXIAL
	CRYSTALLIZATION WITH ION BEAM MIXING
	G. YACHIDA, Y. HOSHINO, and J. NAKATA71
13.	THE FORMATION OF ULTRATHIN SIC LAYER BY OXYGEN AND SILICON IMPLANTATION
	INTO 4H-SiC(0001) SUBSTRATE
	S. TAKADA, Y. HOSHINO, and J. NAKATA · · · · · 75
AII	THOR INDEX